

# Francesco Montalenti

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

150  
papers

3,753  
citations

30  
h-index

56  
g-index

153  
ext. papers

3,991  
ext. citations

4.4  
avg, IF

5.14  
L-index

#	Paper	IF	Citations
150	Stress-Induced Acceleration and Ordering in Solid-State Dewetting.. <i>Physical Review Letters</i> , <b>2022</b> , 128, 026101	7.4	0
149	Atomic-scale insights on the formation of ordered arrays of edge dislocations in Ge/Si(001) films via molecular dynamics simulations.. <i>Scientific Reports</i> , <b>2022</b> , 12, 3235	4.9	2
148	Machine learning potential for interacting dislocations in the presence of free surfaces.. <i>Scientific Reports</i> , <b>2022</b> , 12, 3760	4.9	0
147	Nature and Shape of Stacking Faults in 3C-SiC by Molecular Dynamics Simulations. <i>Physica Status Solidi (B): Basic Research</i> , <b>2021</b> , 258, 2000598	1.3	0
146	Thermodynamic driving force in the formation of hexagonal-diamond Si and Ge nanowires. <i>Applied Surface Science</i> , <b>2021</b> , 545, 148948	6.7	2
145	Prismatic Ge-rich inclusions in the hexagonal SiGe shell of GaP-Si-SiGe nanowires by controlled faceting. <i>Nanoscale</i> , <b>2021</b> , 13, 9436-9445	7.7	
144	Faceting of Si and Ge crystals grown on deeply patterned Si substrates in the kinetic regime: phase-field modelling and experiments. <i>Scientific Reports</i> , <b>2021</b> , 11, 18825	4.9	1
143	Sunburst pattern by kinetic segregation in core-shell nanowires: A phase-field study. <i>Applied Surface Science</i> , <b>2020</b> , 517, 146056	6.7	4
142	Self-Assembly of Nanovoids in Si Microcrystals Epitaxially Grown on Deeply Patterned Substrates. <i>Crystal Growth and Design</i> , <b>2020</b> , 20, 2914-2920	3.5	2
141	The origin and nature of killer defects in 3C-SiC for power electronic applications by a multiscale atomistic approach. <i>Journal of Materials Chemistry C</i> , <b>2020</b> , 8, 8380-8392	7.1	9
140	Selective Area Epitaxy of GaAs/Ge/Si Nanomembranes: A Morphological Study. <i>Crystals</i> , <b>2020</b> , 10, 57	2.3	4
139	Kinetic Control of Morphology and Composition in Ge/GeSn Core/Shell Nanowires. <i>ACS Nano</i> , <b>2020</b> , 14, 2445-2455	16.7	12
138	Reduction of threading dislocation density beyond the saturation limit by optimized reverse grading. <i>Physical Review Materials</i> , <b>2020</b> , 4,	3.2	10
137	Controlling the relaxation mechanism of low strain Si <sub>1-x</sub> Gex/Si(001) layers and reducing the threading dislocation density by providing a preexisting dislocation source. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 215305	2.5	4
136	Computational Analysis of Low-Energy Dislocation Configurations in Graded Layers. <i>Crystals</i> , <b>2020</b> , 10, 661	2.3	3
135	Reentrant Behavior of the Density vs. Temperature of Indium Islands on GaAs(111)A. <i>Nanomaterials</i> , <b>2020</b> , 10,	5.4	1
134	Molecular dynamics simulations of extended defects and their evolution in 3C-BiC by different potentials. <i>Modelling and Simulation in Materials Science and Engineering</i> , <b>2020</b> , 28, 015002	2	8

133	Structure and Stability of Partial Dislocation Complexes in 3C-SiC by Molecular Dynamics Simulations. <i>Materials</i> , <b>2019</b> , 12,	3.5	6
132	Temperature-Dependent Stability of Polytypes and Stacking Faults in SiC: Reconciling Theory and Experiments. <i>Physical Review Applied</i> , <b>2019</b> , 12,	4.3	17
131	Growth and Coalescence of 3C-SiC on Si(111) Micro-Pillars by a Phase-Field Approach. <i>Materials</i> , <b>2019</b> , 12,	3.5	5
130	Dynamics of crosshatch patterns in heteroepitaxy. <i>Physical Review B</i> , <b>2019</b> , 100,	3.3	6
129	Motion of crystalline inclusions by interface diffusion in the proximity of free surfaces. <i>Journal of Nanoparticle Research</i> , <b>2019</b> , 21, 1	2.3	1
128	Competition Between Kinetics and Thermodynamics During the Growth of Faceted Crystal by Phase Field Modeling. <i>Physica Status Solidi (B): Basic Research</i> , <b>2019</b> , 256, 1800518	1.3	17
127	Slip trace-induced terrace erosion. <i>Applied Surface Science</i> , <b>2019</b> , 466, 454-458	6.7	
126	Growth kinetics and morphological analysis of homoepitaxial GaAs fins by theory and experiment. <i>Physical Review Materials</i> , <b>2018</b> , 2,	3.2	20
125	Alignment control of self-ordered three dimensional SiGe nanodots. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 114014	1.8	1
124	Dislocation-Free SiGe/Si Heterostructures. <i>Crystals</i> , <b>2018</b> , 8, 257	2.3	13
123	Misfit-Dislocation Distributions in Heteroepitaxy: From Mesoscale Measurements to Individual Defects and Back. <i>Physical Review Applied</i> , <b>2018</b> , 10,	4.3	6
122	Phase-field simulations of faceted Ge/Si-crystal arrays, merging into a suspended film. <i>Applied Surface Science</i> , <b>2017</b> , 391, 33-38	6.7	16
121	Fully coherent Ge islands growth on Si nano-pillars by selective epitaxy. <i>Materials Science in Semiconductor Processing</i> , <b>2017</b> , 70, 30-37	4.3	1
120	Morphological Evolution of Pit-Patterned Si(001) Substrates Driven by Surface-Energy Reduction. <i>Nanoscale Research Letters</i> , <b>2017</b> , 12, 554	5	23
119	Strain Engineering in Highly Mismatched SiGe/Si Heterostructures. <i>Materials Science in Semiconductor Processing</i> , <b>2017</b> , 70, 117-122	4.3	7
118	Structure, interface abruptness and strain relaxation in self-assisted grown InAs/GaAs nanowires. <i>Applied Surface Science</i> , <b>2017</b> , 395, 29-36	6.7	4
117	A self-ordered, body-centered tetragonal superlattice of SiGe nanodot growth by reduced pressure CVD. <i>Nanotechnology</i> , <b>2017</b> , 28, 485303	3.4	5
116	Three-dimensional SiGe/Si heterostructures: Switching the dislocation sign by substrate under-etching. <i>Physical Review Materials</i> , <b>2017</b> , 1,	3.2	4

115	Modeling the competition between elastic and plastic relaxation in semiconductor heteroepitaxy: From cyclic growth to flat films. <i>Physical Review B</i> , <b>2016</b> , 94,	3.3	14
114	Elastic and Plastic Stress Relaxation in Highly Mismatched SiGe/Si Crystals. <i>MRS Advances</i> , <b>2016</b> , 1, 3403-3408	3.4	1
113	Continuum modelling of semiconductor heteroepitaxy: an applied perspective. <i>Advances in Physics: X</i> , <b>2016</b> , 1, 331-367	5.1	13
112	From plastic to elastic stress relaxation in highly mismatched SiGe/Si heterostructures. <i>Acta Materialia</i> , <b>2016</b> , 114, 97-105	8.4	7
111	Photodetection in Hybrid Single-Layer Graphene/Fully Coherent Germanium Island Nanostructures Selectively Grown on Silicon Nanotip Patterns. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2016</b> , 8, 2017-26	9.5	25
110	Temperature-controlled coalescence during the growth of Ge crystals on deeply patterned Si substrates. <i>Journal of Crystal Growth</i> , <b>2016</b> , 440, 86-95	1.6	11
109	Highly Mismatched, Dislocation-Free SiGe/Si Heterostructures. <i>Advanced Materials</i> , <b>2016</b> , 28, 884-8	2.4	30
108	Enhancing elastic stress relaxation in SiGe/Si heterostructures by Si pillar necking. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 182112	3.4	3
107	Anisotropic extended misfit dislocations in overcritical SiGe films by local substrate patterning. <i>Nanotechnology</i> , <b>2016</b> , 27, 425301	3.4	1
106	Reduced-Pressure Chemical Vapor Deposition Growth of Isolated Ge Crystals and Suspended Layers on Micrometric Si Pillars. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2016</b> , 8, 26374-26380	9.5	9
105	Dynamics of pit filling in heteroepitaxy via phase-field simulations. <i>Physical Review B</i> , <b>2016</b> , 94,	3.3	14
104	Faceting of Equilibrium and Metastable Nanostructures: A Phase-Field Model of Surface Diffusion Tackling Realistic Shapes. <i>Crystal Growth and Design</i> , <b>2015</b> , 15, 2787-2794	3.5	54
103	InAs/GaAs Sharply Defined Axial Heterostructures in Self-Assisted Nanowires. <i>Nano Letters</i> , <b>2015</b> , 15, 3677-83	11.5	16
102	Imaging Structure and Composition Homogeneity of 300 mm SiGe Virtual Substrates for Advanced CMOS Applications by Scanning X-ray Diffraction Microscopy. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 9031-7	9.5	23
101	Engineered Coalescence by Annealing 3D Ge Microstructures into High-Quality Suspended Layers on Si. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 19219-25	9.5	23
100	Delayed plastic relaxation limit in SiGe islands grown by Ge diffusion from a local source. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 104309	2.5	1
99	Local uniaxial tensile strain in germanium of up to 4% induced by SiGe epitaxial nanostructures. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 083101	3.4	16
98	Fully coherent growth of Ge on free-standing Si(001) nanomesas. <i>Physical Review B</i> , <b>2014</b> , 89,	3.3	30

97	Fine control of plastic and elastic relaxation in Ge/Si vertical heterostructures. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 104306	2.5	21
96	Straining Ge bulk and nanomembranes for optoelectronic applications: a systematic numerical analysis. <i>Semiconductor Science and Technology</i> , <b>2014</b> , 29, 095012	1.8	13
95	Hydrostatic strain enhancement in laterally confined SiGe nanostripes. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	12
94	One-dimensional Ge nanostructures on Si(001) and Si(1 1 10): Dominant role of surface energy. <i>Comptes Rendus Physique</i> , <b>2013</b> , 14, 542-552	1.4	16
93	Onset of vertical threading dislocations in Si <sub>1-x</sub> Ge <sub>x</sub> /Si (001) at a critical Ge concentration. <i>APL Materials</i> , <b>2013</b> , 1, 052109	5.7	13
92	Unexpected Dominance of Vertical Dislocations in High-Misfit Ge/Si(001) Films and Their Elimination by Deep Substrate Patterning (Adv. Mater. 32/2013). <i>Advanced Materials</i> , <b>2013</b> , 25, 4407-4407 <sup>24</sup>		2
91	Unexpected dominance of vertical dislocations in high-misfit ge/si(001) films and their elimination by deep substrate patterning. <i>Advanced Materials</i> , <b>2013</b> , 25, 4408-12	24	47
90	Onset of plastic relaxation in the growth of Ge on Si(001) at low temperatures: Atomic-scale microscopy and dislocation modeling. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	11
89	Self-organized evolution of Ge/Si(001) into intersecting bundles of horizontal nanowires during annealing. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 083109	3.4	15
88	Anomalous smoothing preceding island formation during growth on patterned substrates. <i>Physical Review Letters</i> , <b>2012</b> , 109, 156101	7.4	34
87	Monolithic growth of ultrathin Ge nanowires on Si(001). <i>Physical Review Letters</i> , <b>2012</b> , 109, 085502	7.4	73
86	Density functional study of the decomposition pathways of SiH <sub>4</sub> and GeH <sub>4</sub> at the Si(100) and Ge(100) surfaces. <i>Journal of Physics Condensed Matter</i> , <b>2012</b> , 24, 104002	1.8	1
85	Misfit dislocation gettering by substrate pit-patterning in SiGe films on Si(001). <i>Applied Physics Letters</i> , <b>2012</b> , 101, 013119	3.4	11
84	Formation of Ge nanoripples on vicinal Si (1 1 10): from Stranski-Krastanow seeds to a perfectly faceted wetting layer. <i>Physical Review Letters</i> , <b>2012</b> , 108, 055503	7.4	37
83	Stability of Ge on Si (1 1 10) surfaces and the role of dimer tilting. <i>Physical Review B</i> , <b>2012</b> , 85,	3.3	22
82	Assessing the composition of hetero-epitaxial islands via morphological analysis: an analytical model matching GeSi/Si(001) data. <i>Journal of Physics Condensed Matter</i> , <b>2012</b> , 24, 104018	1.8	9
81	Dislocation engineering in SiGe heteroepitaxial films on patterned Si (001) substrates. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 121908	3.4	9
80	Self-Ordering of Misfit Dislocation Segments in Epitaxial SiGe Islands on Si(001). <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 044310	2.5	5

79	Modeling the evolution of germanium islands on silicon(001) thin films <b>2011</b> , 211-246		3
78	Strained MOSFETs on ordered SiGe dots. <i>Solid-State Electronics</i> , <b>2011</b> , 65-66, 81-87	1.7	2
77	Assessing the delay of plastic relaxation onset in SiGe islands grown on pit-patterned Si(001) substrates. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 033106	3.4	19
76	How pit facet inclination drives heteroepitaxial island positioning on patterned substrates. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	37
75	Temperature-dependent evolution of the wetting layer thickness during Ge deposition on Si(001). <i>Nanotechnology</i> , <b>2011</b> , 22, 285704	3.4	15
74	Si/Ge exchange mechanisms at the Ge(105) surface. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	6
73	Self-assembled GaAs islands on Si by droplet epitaxy. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 053101	3.4	18
72	Collective shape oscillations of SiGe islands on pit-patterned Si(001) substrates: a coherent-growth strategy enabled by self-regulated intermixing. <i>Physical Review Letters</i> , <b>2010</b> , 105, 166102	7.4	29
71	Optimal Growth Conditions for Selective Ge Islands Positioning on Pit-Patterned Si(001). <i>Nanoscale Research Letters</i> , <b>2010</b> , 5, 1873-7	5	12
70	Aspect-ratio-dependent driving force for nonuniform alloying in Stranski-Krastanow islands. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	21
69	Crystallinity and microstructure in Si films grown by plasma-enhanced chemical vapor deposition: A simple atomic-scale model validated by experiments. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 051904	3.4	16
68	Ab initio study of the diffusion and decomposition pathways of SiH <sub>x</sub> species on Si(100). <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	14
67	Key role of the wetting layer in revealing the hidden path of Ge/Si(001) Stranski-Krastanow growth onset. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	87
66	A fast computational method for determining equilibrium concentration profiles in intermixed nanoislands. <i>Journal of Physics Condensed Matter</i> , <b>2009</b> , 21, 084217	1.8	9
65	Strain and strain-release engineering at epitaxial SiGe islands on Si(0 0 1) for microelectronic applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2009</b> , 159-160, 90-94	3.1	8
64	Phenomenological model of nanocrystalline silicon film formation by plasma-enhanced chemical vapor deposition. <i>Optoelectronics, Instrumentation and Data Processing</i> , <b>2009</b> , 45, 322-327	0.6	
63	Enhanced relaxation and intermixing in Ge islands grown on pit-patterned Si(001) substrates. <i>Physical Review Letters</i> , <b>2009</b> , 102, 025502	7.4	78
62	Atomistic approach for Boron Transient Enhanced Diffusion and clustering <b>2008</b> ,		2

61	Understanding the elastic relaxation mechanisms of strain in Ge islands on pit-patterned Si(001) substrates. <i>Journal of Physics Condensed Matter</i> , <b>2008</b> , 20, 454217	1.8	12
60	Intermixing in heteroepitaxial islands: fast, self-consistent calculation of the concentration profile minimizing the elastic energy. <i>New Journal of Physics</i> , <b>2008</b> , 10, 083039	2.9	29
59	Modeling the plastic relaxation onset in realistic SiGe islands on Si(001). <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	55
58	Thermal-hydrogen promoted selective desorption and enhanced mobility of adsorbed radicals in silicon film growth. <i>Physical Review Letters</i> , <b>2008</b> , 100, 046105	7.4	15
57	First principles study of GeBi exchange mechanisms at the Si(001) surface. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 191908	3.4	21
56	Detailed Analysis of the Shape-dependent Deformation Field in 3D Ge Islands <b>2008</b> , 421-438		10
55	A multiscale model of the plasma assisted deposition of crystalline silicon. <i>Surface and Coatings Technology</i> , <b>2007</b> , 201, 8863-8867	4.4	8
54	Interaction of SiH <sub>x</sub> precursors with hydrogen-covered Si surfaces: Impact dynamics and adsorption sites. <i>Surface Science</i> , <b>2007</b> , 601, 3970-3973	1.8	4
53	Vertical and lateral ordering of Ge islands grown on Si(001): theory and experiments. <i>Journal of Physics Condensed Matter</i> , <b>2007</b> , 19, 225001	1.8	16
52	Quantitative estimate of H abstraction by thermal SiH <sub>3</sub> on hydrogenated Si(001)(2×1). <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	18
51	Atomic-scale modeling of next-layer nucleation and step flow at the Ge(105) rebonded-step surface. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	8
50	Delayed Plastic Relaxation on Patterned Si Substrates: Coherent SiGe Pyramids with Dominant {111} Facets. <i>Physical Review Letters</i> , <b>2007</b> , 98,	7.4	91
49	Critical shape and size for dislocation nucleation in Si <sub>1-x</sub> Ge <sub>x</sub> islands on Si(001). <i>Physical Review Letters</i> , <b>2007</b> , 99, 235505	7.4	48
48	Accurate and analytical strain mapping at the surface of Ge/Si(0 0 1) islands by an improved flat-island approximation. <i>Surface Science</i> , <b>2006</b> , 600, 4777-4784	1.8	16
47	Impact-driven effects in thin-film growth: steering and transient mobility at the Ag(110) surface. <i>Nanotechnology</i> , <b>2006</b> , 17, 3556-62	3.4	6
46	Multiscale modeling of island nucleation and growth during Cu(100) homoepitaxy. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	10
45	Self-ordering of a Ge island single layer induced by Si overgrowth. <i>Physical Review Letters</i> , <b>2006</b> , 96, 106102	7.4	42
44	Spontaneous Ge island ordering promoted by partial silicon capping. <i>Materials Science in Semiconductor Processing</i> , <b>2006</b> , 9, 823-827	4.3	

43	Binding sites for SiH <sub>2</sub> /Si(0 0 1): A combined ab initio, tight-binding, and classical investigation. <i>Surface Science</i> , <b>2006</b> , 600, 4445-4453	1.8	7
42	Accelerated Molecular Dynamics Methods <b>2005</b> , 629-648		12
41	Atomistic modeling of step formation and step bunching at the Ge(105) surface. <i>Surface Science</i> , <b>2005</b> , 591, 23-31	1.8	19
40	Atomistic simulation of a 60° shuffle dislocation segment migrating in a Ge/SiGe(001) epitaxial film. <i>Journal of Physics Condensed Matter</i> , <b>2005</b> , 17, 7505-7515	1.8	7
39	Strain-induced ordering of small Ge islands in clusters at the surface of multilayered SiGe nanostructures. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 261919	3.4	36
38	Stability of shuffle and glide dislocation segments with increasing misfit in Ge <sub>1-x</sub> Si <sub>x</sub> (001) epitaxial layers. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 041912	3.4	16
37	Fast isotropic adatom diffusion on Ge(105) dot facets. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	20
36	Atomic-scale pathway of the pyramid-to-dome transition during ge growth on Si(001). <i>Physical Review Letters</i> , <b>2004</b> , 93, 216102	7.4	104
35	Structure and mobility of defects formed from collision cascades in MgO. <i>Physical Review Letters</i> , <b>2004</b> , 92, 115505	7.4	90
34	Diffusion and stability of small vacancy clusters on Cu(100) simulation study. <i>Surface Science</i> , <b>2004</b> , 565, 289-299	1.8	12
33	Electronic and elastic contributions in the enhanced stability of Ge(105) under compressive strain. <i>Surface Science</i> , <b>2004</b> , 556, 121-128	1.8	71
32	Relaxed SiGe heteroepitaxy on Si with very thin buffer layers: experimental LEPECVD indications and an interpretation based on strain-dependent dislocation nature. <i>Microelectronic Engineering</i> , <b>2004</b> , 76, 290-296	2.5	6
31	Leapfrog-induced selective faceting in the growth of missing-row (110) surfaces. <i>Chemical Physics Letters</i> , <b>2004</b> , 398, 50-55	2.5	4
30	Theoretical evidence for fast H-divacancy rotation on H/Pd(111). <i>Chemical Physics Letters</i> , <b>2004</b> , 400, 163-168	2.5	3
29	Formation of strain-induced Si-rich and Ge-rich nanowires at misfit dislocations in SiGe: A model supported by photoluminescence data. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 2895-2897	3.4	16
28	Transition-path spectra at metal surfaces. <i>Surface Science</i> , <b>2003</b> , 543, 141-152	1.8	8
27	Extending the Time Scale in Atomistic Simulation of Materials. <i>Annual Review of Materials Research</i> , <b>2002</b> , 32, 321-346	12.8	543
26	Spontaneous atomic shuffle in flat terraces: Ag(100). <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	19



25	Exploiting past visits or minimum-barrier knowledge to gain further boost in the temperature-accelerated dynamics method. <i>Journal of Chemical Physics</i> , <b>2002</b> , 116, 4819	3.9	53
24	Crossover among structural motifs in transition and noble-metal clusters. <i>Journal of Chemical Physics</i> , <b>2002</b> , 116, 3856-3863	3.9	383
23	Simulation of growth of Cu on Ag(001) at experimental deposition rates. <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	50
22	Cell cycle effects of gemcitabine. <i>International Journal of Cancer</i> , <b>2001</b> , 93, 401-8	7.5	62
21	Applying Accelerated Molecular Dynamics to Crystal Growth. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 226, 21-27	1.3	17
20	Normal-incidence steering effect in crystal growth: Ag/Ag(100). <i>Physical Review B</i> , <b>2001</b> , 64,	3.3	41
19	Closing the gap between experiment and theory: crystal growth by temperature accelerated dynamics. <i>Physical Review Letters</i> , <b>2001</b> , 87, 126101	7.4	64
18	Diffusion of Adatoms and Small Clusters on Missing-Row-Reconstructed Surfaces. <i>NATO Science Series Series II, Mathematics, Physics and Chemistry</i> , <b>2001</b> , 237-245		
17	Comment on Scaling behavior of one-dimensional Pt chains migration on Pt(110)-(1 $\times$ 1) surface. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , <b>2000</b> , 277, 185-187	2.3	
16	Probability of dimer reassociation in two dimensions. <i>Physical Review E</i> , <b>2000</b> , 61, 3411-6	2.4	4
15	Long jumps in the strong-collision model. <i>Physical Review E</i> , <b>2000</b> , 61, 6344-50	2.4	17
14	Diffusion of one-dimensional clusters on Au and Pt(110) (1 $\times$ 1). <i>Surface Science</i> , <b>2000</b> , 454-456, 575-578	1.8	5
13	Mobility of atomic chains on channeled surfaces. <i>Journal of Chemical Physics</i> , <b>2000</b> , 113, 349-356	3.9	7
12	Leapfrog Diffusion Mechanism for One-Dimensional Chains on Missing-Row Reconstructed Surfaces. <i>Physical Review Letters</i> , <b>1999</b> , 82, 1498-1501	7.4	88
11	Universal law for piecewise dimer diffusion. <i>Physical Review B</i> , <b>1999</b> , 60, 11102-11109	3.3	8
10	Long-jump probabilities in a BGK model for surface diffusion. <i>Chemical Physics Letters</i> , <b>1999</b> , 315, 153-157.	5	9
9	Measuring the complexity of cell cycle arrest and killing of drugs: Kinetics of phase-specific effects induced by Taxol <b>1999</b> , 37, 113-124		34
8	Dimers diffusion on (110) (1 $\times$ 1) metal surfaces. <i>Surface Science</i> , <b>1999</b> , 432, 27-36	1.8	24

7	An MD study of adatom self-diffusion on Au(110) surfaces. <i>Surface Science</i> , <b>1999</b> , 433-435, 445-448	1.8	13
6	Jumps and concerted moves in Cu, Ag, and Au(110) adatom self-diffusion. <i>Physical Review B</i> , <b>1999</b> , 59, 5881-5891	3.3	127
5	Ab-initio adiabatic noble gas-metal interaction: the role of the induced polarization charge. <i>Surface Science</i> , <b>1998</b> , 401, L383-L387	1.8	9
4	Simulating cancer-cell kinetics after drug treatment: Application to cisplatin on ovarian carcinoma. <i>Physical Review E</i> , <b>1998</b> , 57, 5877-5887	2.4	34
3	Competing mechanisms in adatom diffusion on a channeled surface: Jumps versus metastable walks. <i>Physical Review B</i> , <b>1998</b> , 58, 3617-3620	3.3	50
2	Ab initio results for the adiabatic atom-surface interaction for helium and neon on a simple metal. <i>Surface Science</i> , <b>1996</b> , 364, L595-L599	1.8	18
1	Charge transfer in chemisorption: N and Si on Al. <i>Solid State Communications</i> , <b>1996</b> , 99, 7-11	1.6	2